

Response Under 37 C.F.R. § 1.116 - Expedited Procedure
Examining Group 2823

IN THE UNITED STATES PATENT AND TRADEMARK OFFICEIn re the application of: Wilk *et al.*

Docket: TI-24742

Serial No.: 09/176,422

Examiner: N. Berezny

Filed: 10/21/98

Art Unit: 2823 **FAX COPY RECEIVED**

For: Low Temperature Method For Forming A Thin, Uniform Oxide

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AMENDMENT PURSUANT TO 37 C.F.R. § 1.116

January 26, 2001

Ass't Commissioner for Patents
Washington, DC 20231

FACSIMILE CERTIFICATE	
I hereby certify that this correspondence is being transmitted by Facsimile to the Patent and Trademark Office in accordance with 37 C.F.R. § 1.6d on	
<i>February 2</i>	2001
<i>Tina Rendon</i>	
Tina Rendon	

Examiner:

In response to the Office Action dated December 6, 2000, please consider the following remarks.

REMARKS

Claims 1-25 are pending in the present application and have been rejected by Examiner.

Applicants respectfully request reconsideration of the rejection.

1. The Office Action objected to claims 23 - 25. Applicants disagree with this objection. Claim 24 is exemplary. Claim 24 further limits claim 18, in that it limits the types of gate oxide films—created by exposing the silicon surface to an atmosphere including ozone—that would infringe this claim. Applicants submit that a process—that used the steps in the claim—to make a gate oxide with a breakdown strength of 8 MV/cm would infringe claim 18, but not infringe claim 24.

2. The Office Action rejected claim 18 under 35 U.S.C. § 103 as being unpatentable over Fujishiro *et al.* (Fujishiro '571) in combination with Nayar *et al.* (Nayar article). Claim 18's limitations include "exposing the silicon surface to an atmosphere including ozone, while